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Form PTO-1595 (Rev. 09/04) CMB No. 0651-0027 (axp. 6/30/2005)	U.S. DEPARTMENT OF COMMERCE United States Patent and Trademark Office		
RECORDATION FORM COVER SHEET			
PATENTS ONLY To the Director of the U.S. Patent and Trademark Office: Please record the attached documents or the new address(es) below.			
Name of conveying party(ies)/Execution Date(s):	2. Name and address of receiving party(ies)		
Ecole Polytechnique Fédérale de Lausanne	Name: Innovative Silicon S.A.		
Ecole Polytechnique rederate de Ladaanno	Internal Address:		
'			
Evacution Data(s) Basember & 2002			
Execution Date(s) December 6, 2002 Additional name(s) of conveying party(les) attached? Yes No	Street Address: PSE - Batiment B		
3. Nature of conveyance:	·		
Assignment Merger	City: Lausanne		
Security Agreement Change of Name	State:		
Government Interest Assignment	Country: Switzerland Zip: CH-1015		
Executive Order 9424, Confirmatory License			
Other	Additional name(s) & address(es) attached? Yes V No		
4. Application or patent number(s): A. Patent Application No.(s) 10/487,162	document is being filed together with a new application. B. Patent No.(s)		
Additional numbers at	tached? Yes No		
5. Name and address to whom correspondence concerning document should be mailed:	6. Total number of applications and patents involved:		
Name: Neil A. Steinberg	7. Total fee (37 CFR 1.21(h) & 3.41) \$_40.00		
Internal Address:	Authorized to be charged by credit card		
	Authorized to be charged to deposit account		
Street Address: 2665 Marine Way, Suite 1150	Enclosed		
Chicoc Fradi debt <u>most marrie 1123</u>	None required (government interest not affecting title)		
City; Mountain View	8. Payment Information		
State: CA Zip: 94043	a. Credit Card Last 4 Numbers Expiration Date		
Phone Number: 650-968-8079			
Fax Number: 650-968-8102	b. Deposit Account Number 50-0763		
Email Address: neils@swpatentlaw.com	Authorized User Name Neil A. Steinberg		
9. Signature:	Manch 2 2005		
Signature	March 3, 2005		
Neil A. Steinberg	Total number of pages including cover		
Name of Person Signing	sheet, attachments, and documents:		

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AGREEMENT

between

Ecole Polytechnique Fédérale de Lausanne,

CH-1015 Lausanne, Switzerland, represented by Prof. Declercq, Elead of Electronics Laboratory (hereafter referred to as "EPFL")

on the one part.

and

Innovative Silicon SA

PSE-B

CH-1015 Lausanne, Switzerland represented by André Borschberg and Pierre Fazan

(hereafter referred to as "ISi")

on the second part,

and

Pierre Fazan Av. Du Carroz 1 CH-1110 Morges

and

Serguei Okhonin Jolimont 2 CH-1005 Lausanne

anđ

André Borschberg 9 route de Lausanne CH-1260 Nyon

and

Luc Bauer 6 ch. Des Clos 2073Enges

(hereafter collectively referred to as "the Founders")

on the third part.

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PATENT

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2002

Preamble

Researchers from the Electronics Laboratory of EPFL and Pierre Fazan Innovative Silicon Solutions at Morges, Switzerland (the latter hereafter referred to as "ISS"), have generated and developed a concept of semiconductor devices exploiting the floating body effect.

In an agreement dated September 11, 2001, EPFL and ISS agreed that patent applications to be filed on this concept shall be jointly owned by ISS and EPFL, namely in a proportion of two thirds for ISS and one third for EPFL.

EPFL and ISS have filed an initial patent application on the above mentioned concept.

On May 22, 2002, the Founders have set up ISi.

By a separate agreement dated September 12, 2002, ISS has assigned to ISi all its rights to the initial patent application.

EPFL and ISi have filed other patent applications on the concept and its applications.

With the aim to allow further development of the concept and its use for the benefit of the public, EPFL is willing to irrevocably fully assign to ISi its co-ownership rights on the said patent applications and to grant a non-exclusive license on certain software and layouts, under the terms and conditions set forth hereafter.

ARTICLE 1 - DEFINITIONS

- Patents

"Patents" shall mean the patent applications filed or to be filed, which are listed in Exhibit 1 hereto, as well as all patents issued from the said patent applications. The text of the 3 patent applications to be filed is appended in Exhibit 1.

- Technology

"Technology" shall mean the technologies covered by one or more Patents.

- Field

"Field" shall mean semi-conductor memories excluding CMOS imagers and sensors.

- Licensed Items

"Licensed Items" shall mean the software and the layouts defined in Exhibit 2 hereto.

ARTICLE 2 – ASSIGNMENT – LICENSE

2.1 EPFL hereby irrevocably sells, assigns and transfers to ISi, which accepts, any and all its co-ownership rights to the Patents. As a result thereof, ISi shall have sole and full ownership to the Patents, in particular the exclusive right to use and exploit the Technology and the Patents in all fields of applications, including the right to

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manufacture, have manufactured, sell and license products and/or processes based on the Technology and/or the Patents. EPFL agrees, upon ISi request, to execute any documents necessary for effecting the sale, assignment and transfer of the Patents to ISi contemplated hereunder.

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This Agreement is executed in three originals and duly signed by the parties hereto, as printed below:

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Innovative Silicon ISI S.A.

(signature)

Prof. Declereq, Head of Electronics Laboratory

Place and date: Laus innu

(signatur∕es)

A. Borschberg, Director

P. Fazan,

Director

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Pierre Fazan

Place and date: Janana Dec. 6, 2002.
Signature: Janana Janana

Serguei Okhonin

Place and date: buosumue, Bec 6, 2002

Signature:____

André Borschberg

Place and date: (gentine Dec 6 2002

Signature:

Lnc Bauer

Exhibit 1:

Exhibit 2:

Exhibit 3:

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Patent Ap
: List of Patent Ag

a) List of Patent Applications Filed:

Reference	Reference Law firm	Title	Filing Date	Filling Number	Inventors
Case 1	Gressel	Dispositif semi-conductsur, notamment mėmotre DRAM	18.06.01	EP 01810587.4	Pierre Fazan Serguei Okironin
Case 2	Gresset	Proceidé de commande d'un dispositif semi-conducteur	28.03.02	EP 02405247.4	Pleme Fazan Serguei Okhonin
Case 3	Greasel	Dispositi de ratratchissement d'une mémoire	18.04.02	EP 02405314.2	Pierre Fazan Serguei Okhenin
Case 4	Gressel	Provádě pour oréer una charge électrique dans la corpa d'un composant semi-conducteur	18.04.02	EP 02405315.9	Pierre Fazan Serguel Okhonin
Case 5	Gressel	Dispositi semi-conducteur porteur d'une charge électrique	18.04.02	EP 02405316.7	Pleme Fazan Serguei Okhonin
Ę.	ď	Semicondudor Devide	05.08.02	PCT/EP02/05/95	Pietre Fazan Serguei Oktomin
Case 3	#	Data scorage device and retreshing method for use with such device	29.05.02	EP 02977116.8	Pierre Fazen Serguei Okhonin
Case 5	ğ	Semiconductor device	27.08.02	EP02078565.3	Piene Fazan Serguel Okhonin

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st of Patent Applications to be Filed:	
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	% 4	N.A.	Ϋ́,
b) List of Patent Applications to be Filed:	Method and apparatus for controlling semicondustor memory device	Method and apparatus for generating reference current in semiconductor memory device	Sense & Compare ampiller
of Pateni	d o	пБ	ng r
b) Listo	Case 6 UDL	Case 7	Case 10 UDL

Note: The PCT application is the result of a PCT filling combining cases 1,2,4,8, and 9.

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Exhibit 2:

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Exhibit 3:

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